

MTB50P03HDLT4G-VB Datasheet

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 30	0.008 at $V_{GS} = -10$ V	- 75	56 nC
	0.011 at $V_{GS} = -4.5$ V	- 65	

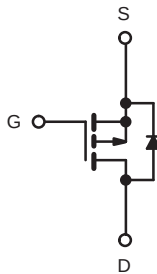
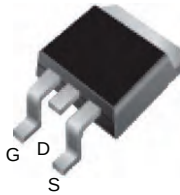
FEATURES

- Halogen-free
- Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested


RoHS
 COMPLIANT

APPLICATIONS

- Load Switch
- Notebook Adaptor Switch

D²PAK (TO-263)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	- 75	A
	$T_C = 70$ °C		- 65	
	$T_A = 25$ °C		-55 ^{a, b}	
	$T_A = 70$ °C		-45 ^{a, b}	
Pulsed Drain Current		I_{DM}	- 200	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	- 4.1	
	$T_A = 25$ °C		- 2.2 ^{a, b}	
Avalanche Current	L = 0.1 mH	I_{AS}	- 75	mJ
Single-Pulse Avalanche Energy		E_{AS}	280	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	250	W
	$T_C = 70$ °C		205	
	$T_A = 25$ °C		3.7 ^{a, b}	
	$T_A = 70$ °C		2.7 ^{a, b}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	$t \leq 10$ s	R_{thJA}	38	46	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	20	25	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

 b. $t = 10$ s.

c. Maximum under Steady State conditions is 85 °C/W.

 d. Based on $T_C = 25$ °C.

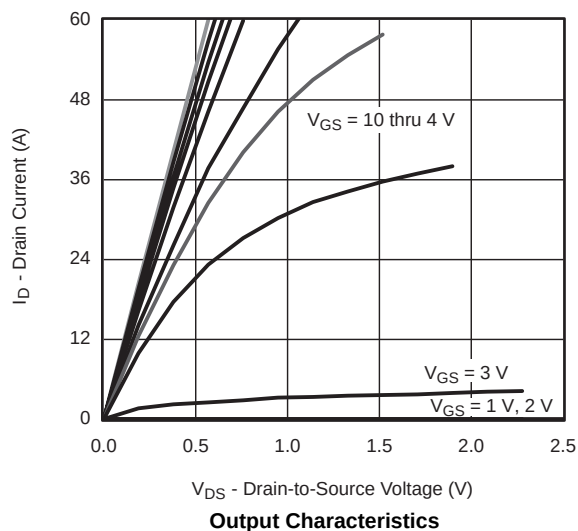
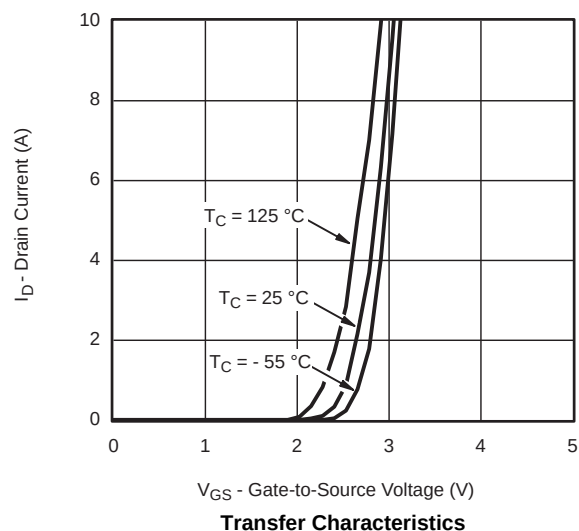
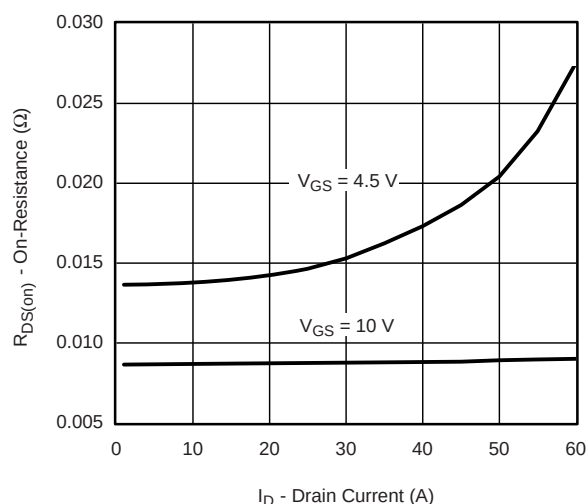
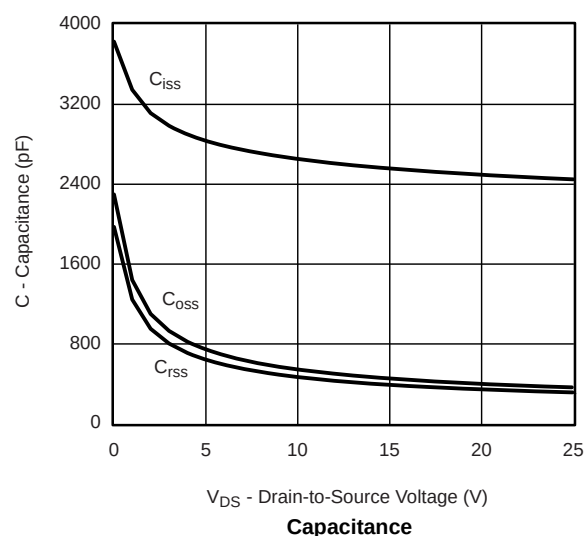
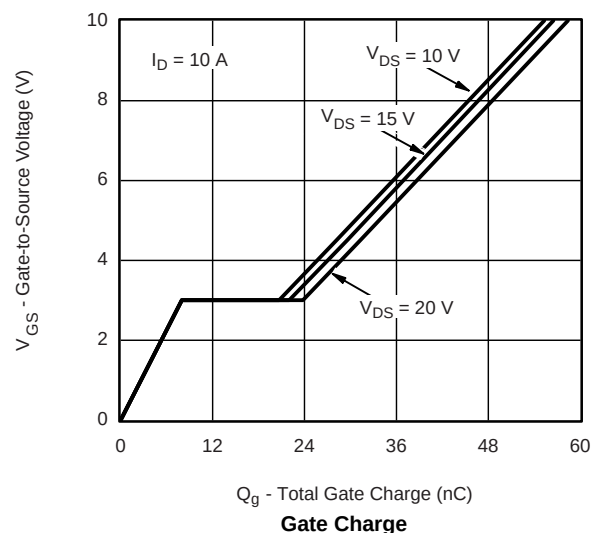
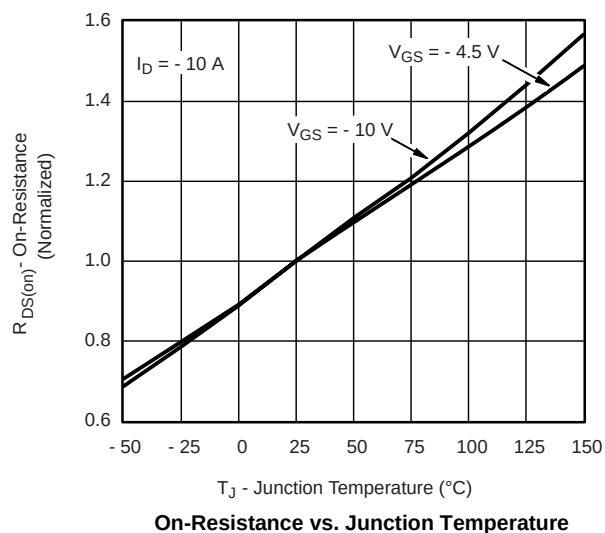
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 34		mV/ °C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 25 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A		0.008		Ω
		V _{GS} = - 4.5 V, I _D = - 8 A		0.011		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 10 A		28		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		4550		pF
Output Capacitance	C _{oss}			1455		
Reverse Transfer Capacitance	C _{rss}			570		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 10 A		115		nC
Gate-Source Charge	Q _{gs}	V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 10 A		56		
Gate-Drain Charge	Q _{gd}			8		
Gate Resistance	R _g			22		
Gate Resistance	R _g	f = 1 MHz	0.5	2.2	4.4	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≅ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		13	25	ns
Rise Time	t _r			12	24	
Turn-Off DelayTime	t _{d(off)}			40	70	
Fall Time	t _f			9	18	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≅ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		48	80	
Rise Time	t _r			92	160	
Turn-Off DelayTime	t _{d(off)}			34	60	
Fall Time	t _f			19	35	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.1	A
Pulse Diode Forward Current	I _{SM}				- 60	
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, dI/dt = 100 A/μs, T _J = 25 °C		27	45	ns
Body Diode Reverse Recovery Charge	Q _{rr}			16	27	nC
Reverse Recovery Fall Time	t _a			12		ns
Reverse Recovery Rise Time	t _b			15		

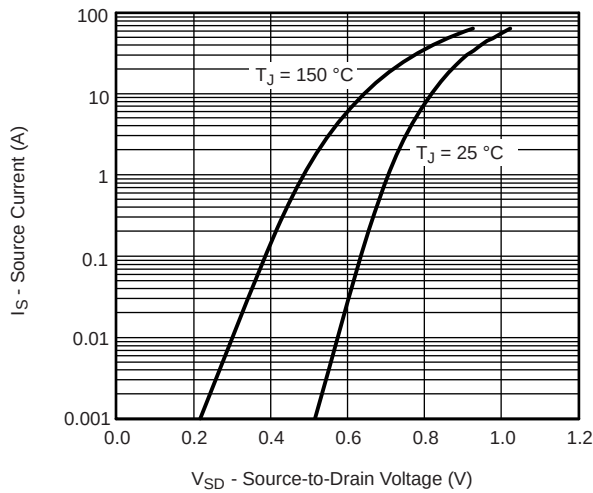
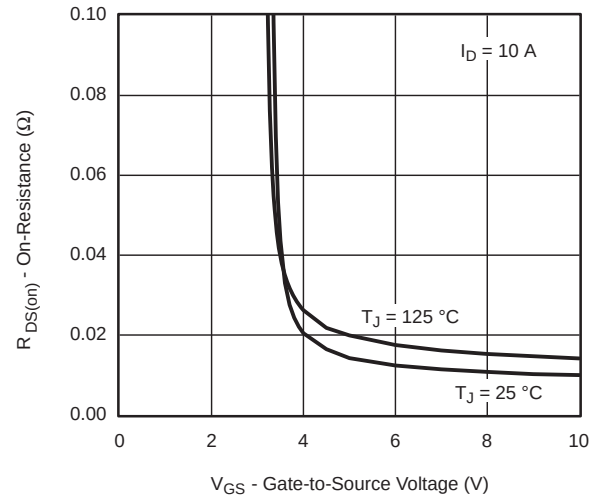
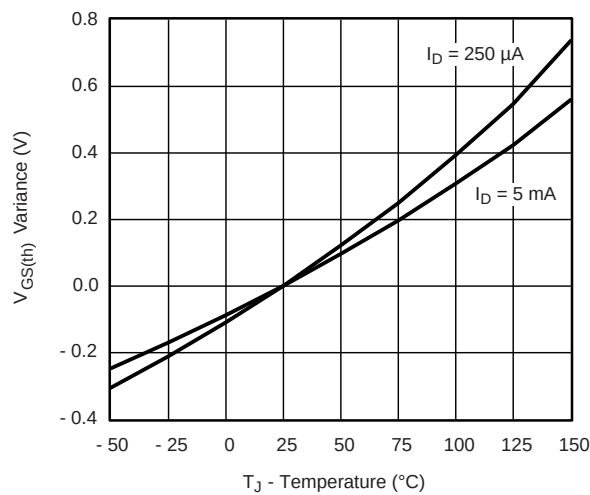
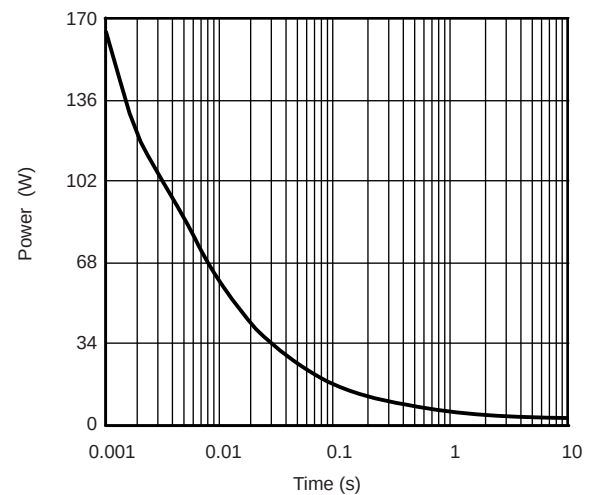
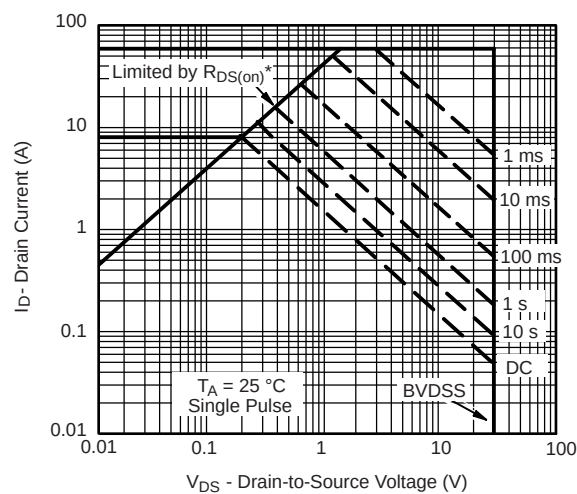
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

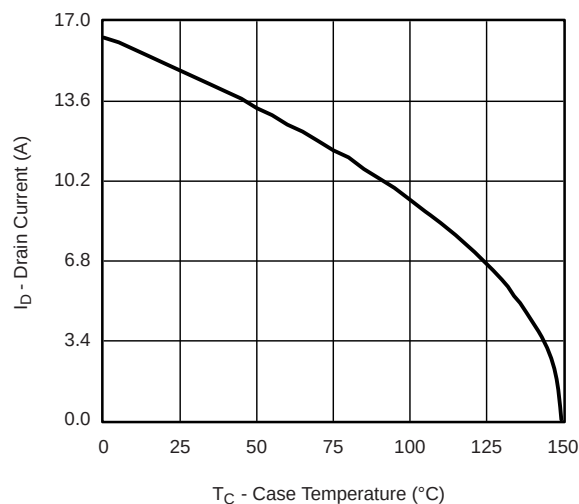
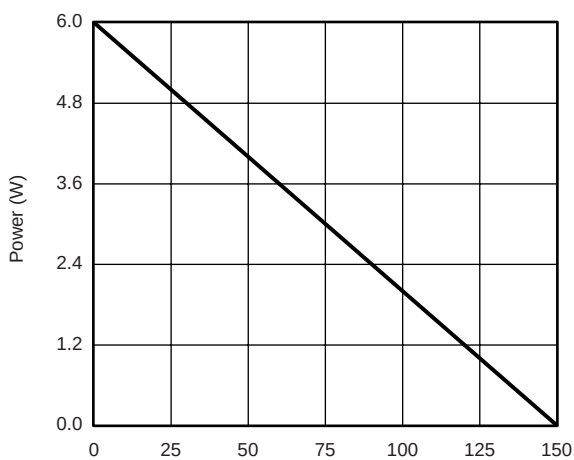
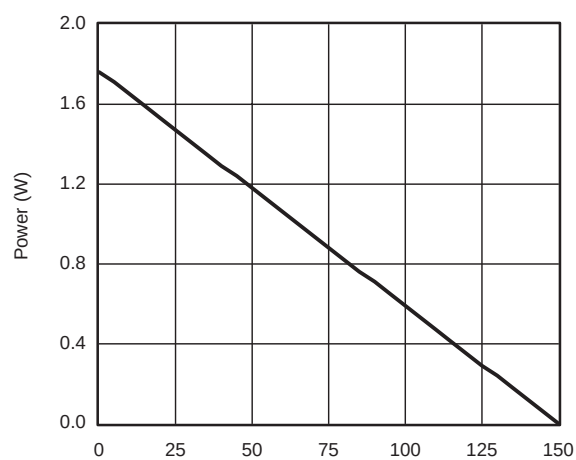
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient


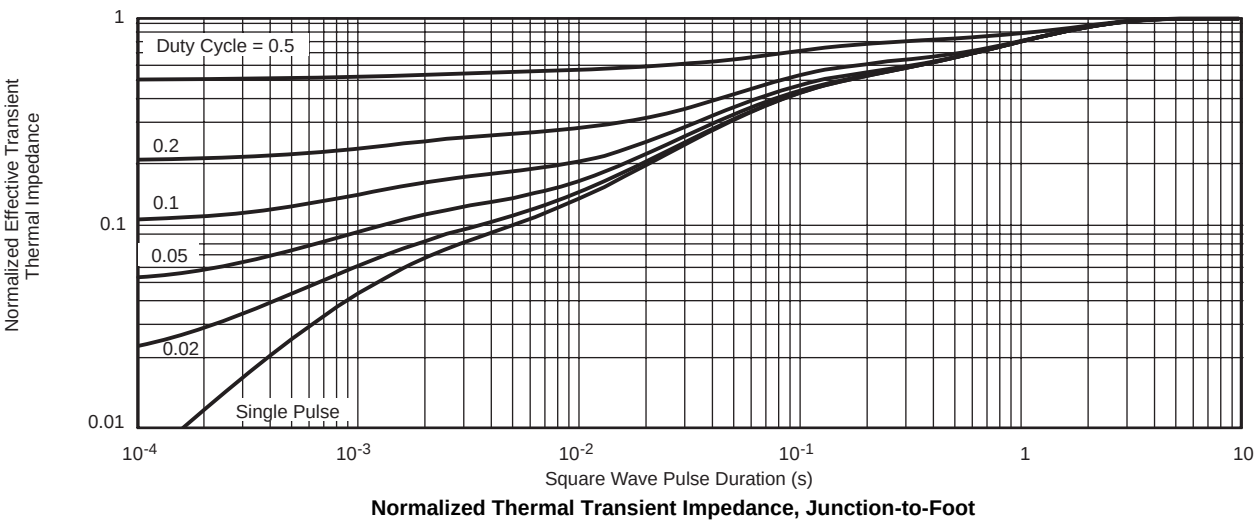
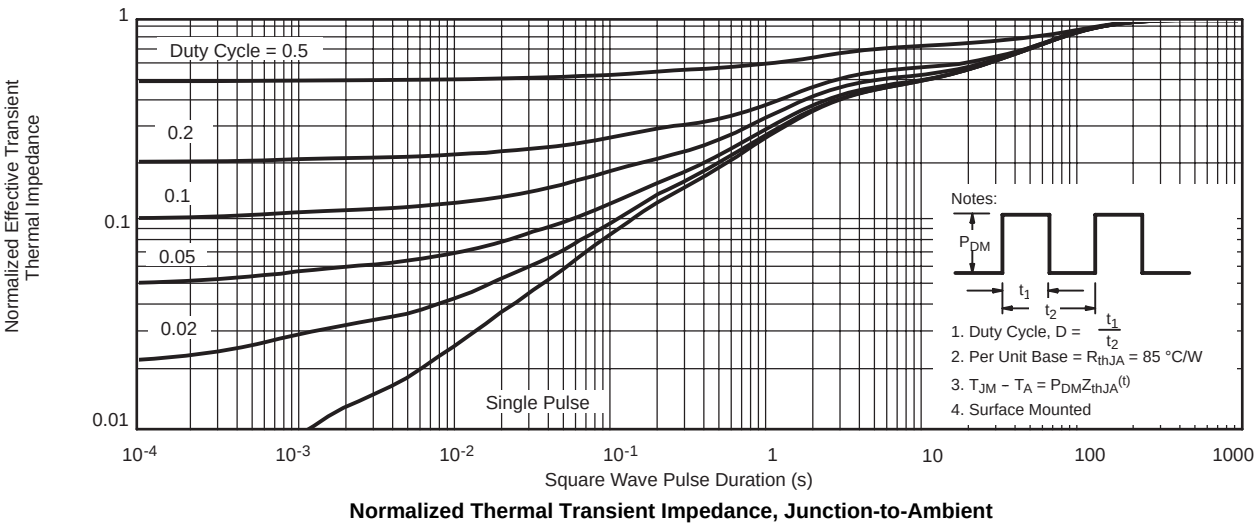
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

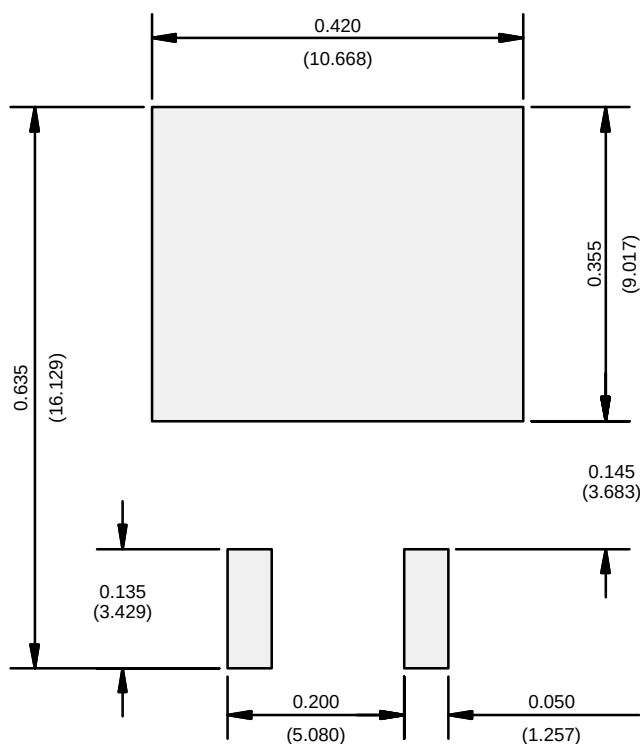
Safe Operating Area

MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Current Derating*

Power, Junction-to-Foot

Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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